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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn250-vqg100

Table of Contents

Introduction	7
Contents	7
Revision History	7
Related Information	7
1 FPGA Array Architecture in Low Power Flash Devices	9
Device Architecture	9
FPGA Array Architecture Support	10
Device Overview	11
Related Documents	20
List of Changes	20
2 Low Power Modes in ProASIC3/E and ProASIC3 nano FPGAs	21
Introduction	21
Power Consumption Overview	21
Static (Idle) Mode	22
User Low Static (Idle) Mode	23
Sleep Mode	25
Shutdown Mode	27
Conclusion	28
Related Documents	28
List of Changes	29
3 Global Resources in Low Power Flash Devices	31
Introduction	31
Global Architecture	31
Global Resource Support in Flash-Based Devices	32
VersaNet Global Network Distribution	33
Chip and Quadrant Global I/Os	35
Spine Architecture	41
Using Clock Aggregation	44
Design Recommendations	46
Conclusion	58
Related Documents	58
List of Changes	59
4 Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs	61
Introduction	61
Overview of Clock Conditioning Circuitry	61
CCC Support in Microsemi's Flash Devices	63
Global Buffers with No Programmable Delays	64
Global Buffer with Programmable Delay	64
Global Buffers with PLL Function	67
Global Input Selections	71
Device-Specific Layout	78

PLL Core Specifications	84
Functional Description	85
Software Configuration	96
Detailed Usage Information	104
Recommended Board-Level Considerations	112
Conclusion	113
Related Documents	113
List of Changes	113
5 FlashROM in Microsemi's Low Power Flash Devices	117
Introduction	117
Architecture of User Nonvolatile FlashROM	117
FlashROM Support in Flash-Based Devices	118
FlashROM Applications	120
FlashROM Security	121
Programming and Accessing FlashROM	122
FlashROM Design Flow	124
Custom Serialization Using FlashROM	129
Conclusion	130
Related Documents	130
List of Changes	130
6 SRAM and FIFO Memories in Microsemi's Low Power Flash Devices	131
Introduction	131
Device Architecture	131
SRAM/FIFO Support in Flash-Based Devices	134
SRAM and FIFO Architecture	135
Memory Blocks and Macros	135
Initializing the RAM/FIFO	148
Software Support	154
Conclusion	157
List of Changes	157
7 I/O Structures in nano Devices	159
Introduction	159
Low Power Flash Device I/O Support	161
nano Standard I/Os	162
I/O Architecture	164
I/O Standards	166
Wide Range I/O Support	166
I/O Features	167
Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout	176
I/O Software Support	177
User I/O Naming Convention	178
I/O Bank Architecture and CCC Naming Conventions	179
Board-Level Considerations	181
Conclusion	182
Related Documents	183
List of Changes	183

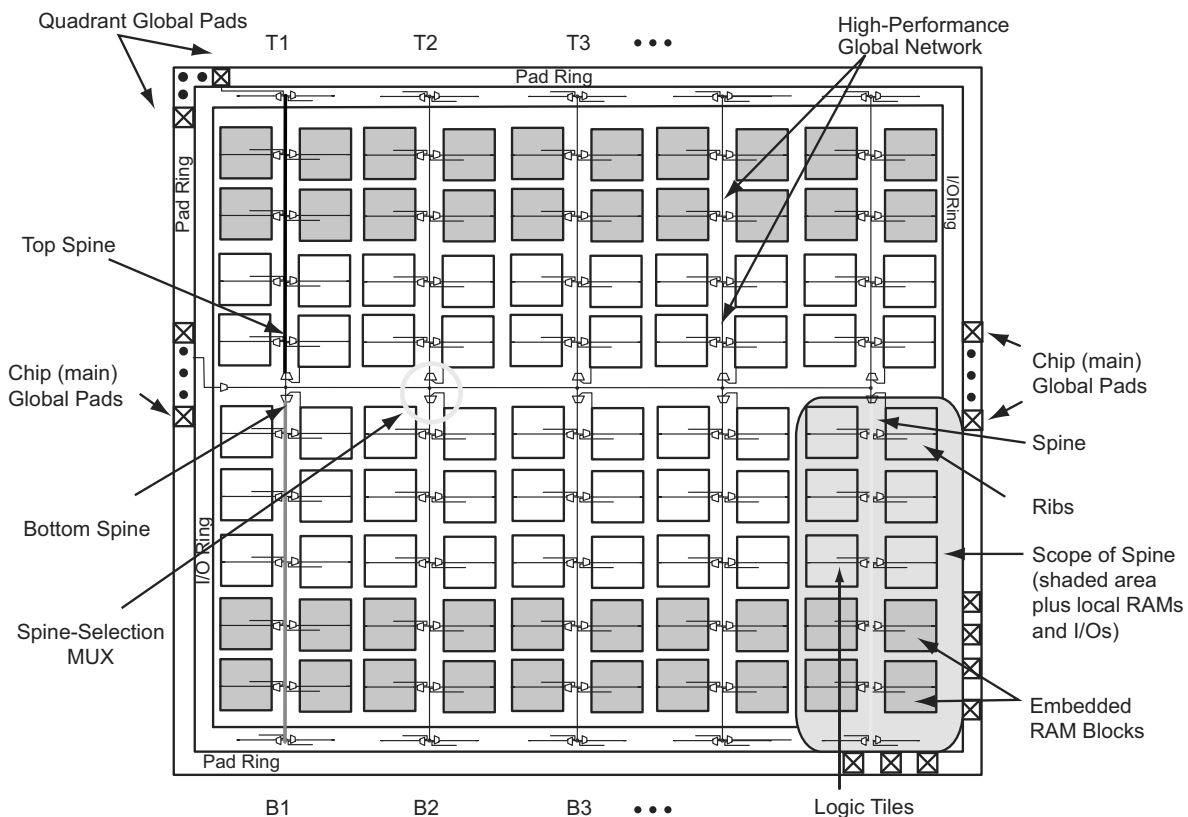
VersaNet Global Network Distribution

One of the architectural benefits of low power flash architecture is the set of powerful, low-delay VersaNet global networks that can access the VersaTiles, SRAM, and I/O tiles of the device. Each device offers a chip global network with six global lines (except for nano 10 k, 15 k, and 20 k gate devices) that are distributed from the center of the FPGA array. In addition, each device (except the 10 k through 30 k gate device) has four quadrant global networks, each consisting of three quadrant global net resources. These quadrant global networks can only drive a signal inside their own quadrant. Each VersaTile has access to nine global line resources—three quadrant and six chip-wide (main) global networks—and a total of 18 globals are available on the device (3×4 regional from each quadrant and 6 global).

Figure 3-1 shows an overview of the VersaNet global network and device architecture for devices 60 k and above. Figure 3-2 and Figure 3-3 on page 34 show simplified VersaNet global networks.

The VersaNet global networks are segmented and consist of spines, global ribs, and global multiplexers (MUXes), as shown in Figure 3-1. The global networks are driven from the global rib at the center of the die or quadrant global networks at the north or south side of the die. The global network uses the MUX trees to access the spine, and the spine uses the clock ribs to access the VersaTile. Access is available to the chip or quadrant global networks and the spines through the global MUXes. Access to the spine using the global MUXes is explained in the "Spine Architecture" section on page 41.

These VersaNet global networks offer fast, low-skew routing resources for high-fanout nets, including clock signals. In addition, these highly segmented global networks offer users the flexibility to create low-skew local clock networks using spines for up to 252 internal/external clocks or other high-fanout nets in low power flash devices. Optimal usage of these low-skew networks can result in significant improvement in design performance.



Note: Not applicable to 10 k through 30 k gate devices

Figure 3-1 • Overview of VersaNet Global Network and Device Architecture

FlashROM Security

Low power flash devices have an on-chip Advanced Encryption Standard (AES) decryption core, combined with an enhanced version of the Microsemi flash-based lock technology (FlashLock®). Together, they provide unmatched levels of security in a programmable logic device. This security applies to both the FPGA core and FlashROM content. These devices use the 128-bit AES (Rijndael) algorithm to encrypt programming files for secure transmission to the on-chip AES decryption core. The same algorithm is then used to decrypt the programming file. This key size provides approximately 3.4×10^{38} possible 128-bit keys. A computing system that could find a DES key in a second would take approximately 149 trillion years to crack a 128-bit AES key. The 128-bit FlashLock feature in low power flash devices works via a FlashLock security Pass Key mechanism, where the user locks or unlocks the device with a user-defined key. Refer to the "Security in Low Power Flash Devices" section on page 235.

If the device is locked with certain security settings, functions such as device read, write, and erase are disabled. This unique feature helps to protect against invasive and noninvasive attacks. Without the correct Pass Key, access to the FPGA is denied. To gain access to the FPGA, the device first must be unlocked using the correct Pass Key. During programming of the FlashROM or the FPGA core, you can generate the security header programming file, which is used to program the AES key and/or FlashLock Pass Key. The security header programming file can also be generated independently of the FlashROM and FPGA core content. The FlashLock Pass Key is not stored in the FlashROM.

Low power flash devices with AES-based security allow for secure remote field updates over public networks such as the Internet, and ensure that valuable intellectual property (IP) remains out of the hands of IP thieves. Figure 5-5 shows this flow diagram.

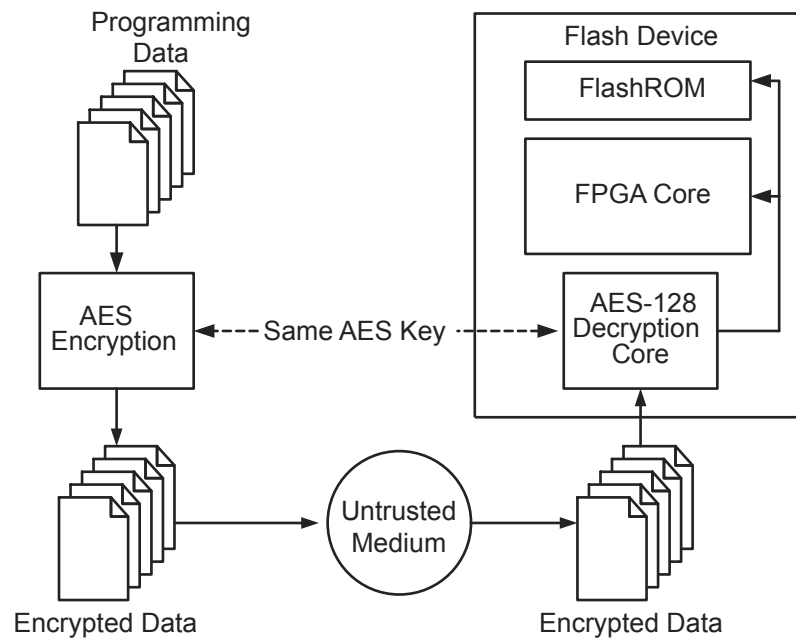


Figure 5-5 • Programming FlashROM Using AES

FlashROM Design Flow

The Microsemi Libero System-on-Chip (SoC) software has extensive FlashROM support, including FlashROM generation, instantiation, simulation, and programming. Figure 5-9 shows the user flow diagram. In the design flow, there are three main steps:

1. FlashROM generation and instantiation in the design
2. Simulation of FlashROM design
3. Programming file generation for FlashROM design

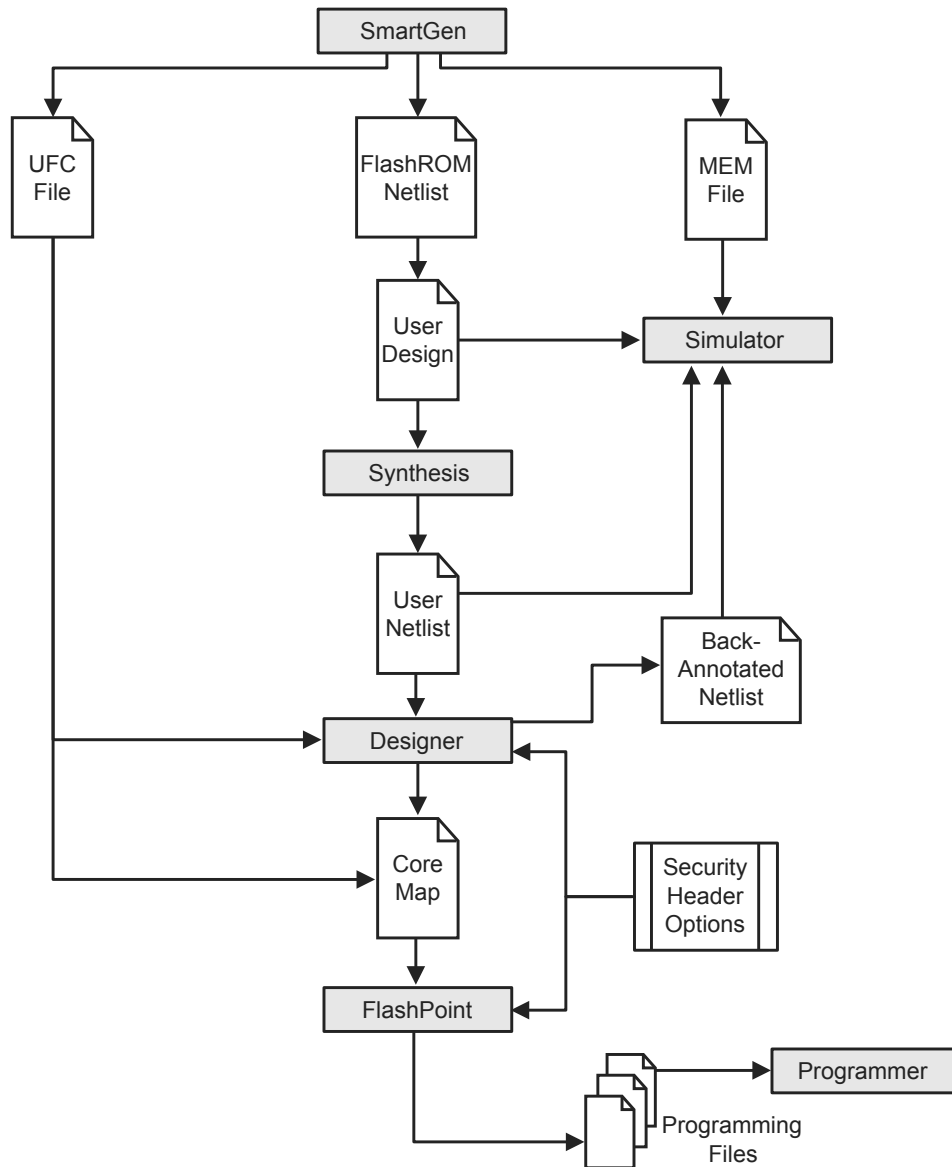


Figure 5-9 • FlashROM Design Flow

6 – SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Introduction

As design complexity grows, greater demands are placed upon an FPGA's embedded memory. Fusion, IGLOO, and ProASIC3 devices provide the flexibility of true dual-port and two-port SRAM blocks. The embedded memory, along with built-in, dedicated FIFO control logic, can be used to create cascading RAM blocks and FIFOs without using additional logic gates.

IGLOO, IGLOO PLUS, and ProASIC3L FPGAs contain an additional feature that allows the device to be put in a low power mode called Flash*Freeze. In this mode, the core draws minimal power (on the order of 2 to 127 μ W) and still retains values on the embedded SRAM/FIFO and registers. Flash*Freeze technology allows the user to switch to Active mode on demand, thus simplifying power management and the use of SRAM/FIFOs.

Device Architecture

The low power flash devices feature up to 504 kbits of RAM in 4,608-bit blocks (Figure 6-1 on page 132 and Figure 6-2 on page 133). The total embedded SRAM for each device can be found in the datasheets. These memory blocks are arranged along the top and bottom of the device to allow better access from the core and I/O (in some devices, they are only available on the north side of the device). Every RAM block has a flexible, hardwired, embedded FIFO controller, enabling the user to implement efficient FIFOs without sacrificing user gates.

In the IGLOO and ProASIC3 families of devices, the following memories are supported:

- 30 k gate devices and smaller do not support SRAM and FIFO.
- 60 k and 125 k gate devices support memories on the north side of the device only.
- 250 k devices and larger support memories on the north and south sides of the device.

In Fusion devices, the following memories are supported:

- AFS090 and AFS250 support memories on the north side of the device only.
- AFS600 and AFS1500 support memories on the north and south sides of the device.

Table 7-10 • Hot-Swap Level 3

Description	Hot-swap while bus idle
Power Applied to Device	Yes
Bus State	Held idle (no ongoing I/O processes during insertion/removal)
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power-down
Example Application	Board bus shared with card bus is "frozen," and there is no toggling activity on the bus. It is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of nano Devices	Compliant

Table 7-11 • Hot-Swap Level 4

Description	Hot-swap on an active bus
Power Applied to Device	Yes
Bus State	Bus may have active I/O processes ongoing, but device being inserted or removed must be idle.
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power-down
Example Application	There is activity on the system bus, and it is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of nano Devices	Compliant

For Level 3 and Level 4 compliance with the nano devices, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Electrostatic Discharge Protection

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All nano devices are qualified to the Human Body Model (HBM) and the Charged Device Model (CDM).

Table 7-12 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in nano Devices

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTTL/LVCMOS	No	Yes	Yes*	Enabled/Disabled	
LVCMOS 2.5 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.2 V	No	Yes	No	Enabled/Disabled	

* Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.

5 V Input and Output Tolerance

nano devices can be made 5 V–input–tolerant for certain I/O standards by using external level shifting techniques. 5 V output compliance can be achieved using certain I/O standards.

Table 7-5 on page 163 shows the I/O standards that support 5 V input tolerance. Only 3.3 V LVTTTL/LVCMOS standards support 5 V output tolerance.

5 V Input Tolerance

I/Os can support 5 V input tolerance when LVTTTL 3.3 V or LVCMOS 3.3 V configurations are used (see Table 7-12). There are three recommended solutions for achieving 5 V receiver tolerance (see Figure 7-5 on page 172 to Figure 7-7 on page 173 for details of board and macro setups). All the solutions meet a common requirement of limiting the voltage at the input to 3.6 V or less. In fact, the I/O absolute maximum voltage rating is 3.6 V, and any voltage above 3.6 V may cause long-term gate oxide failures.

Solution 1

The board-level design must ensure that the reflected waveform at the pad does not exceed the limits provided in the recommended operating conditions in the datasheet. This is a requirement to ensure long-term reliability.

This solution requires two board resistors, as demonstrated in Figure 7-5 on page 172. Here are some examples of possible resistor values (based on a simplified simulation model with no line effects and 10 Ω transmitter output resistance, where $R_{tx_out_high} = (V_{CCI} - V_{OH}) / I_{OH}$ and $R_{tx_out_low} = V_{OL} / I_{OL}$).

Example 1 (high speed, high current):

$$R_{tx_out_high} = R_{tx_out_low} = 10 \Omega$$

$$R1 = 36 \Omega (\pm 5\%), P(r1)_{min} = 0.069 \Omega$$

$$R2 = 82 \Omega (\pm 5\%), P(r2)_{min} = 0.158 \Omega$$

$$I_{max_tx} = 5.5 \text{ V} / (82 \times 0.95 + 36 \times 0.95 + 10) = 45.04 \text{ mA}$$

$$t_{RISE} = t_{FALL} = 0.85 \text{ ns at } C_{pad_load} = 10 \text{ pF (includes up to 25\% safety margin)}$$

$$t_{RISE} = t_{FALL} = 4 \text{ ns at } C_{pad_load} = 50 \text{ pF (includes up to 25\% safety margin)}$$

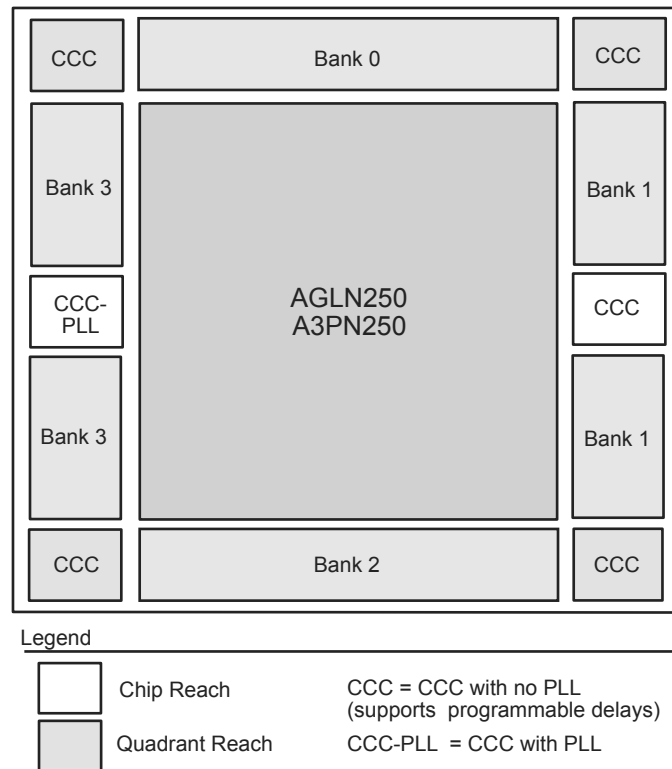


Figure 7-12 • I/O Bank Architecture of AGLN250/A3PN250 Devices

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions and Packaging" chapter of the appropriate device datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO*, *ProASIC3*, *SmartFusion*, and *Fusion Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

Table 9-2 • DDR I/O Options (continued)

DDR Register Type	I/O Type	I/O Standard	Sub-Options	Comments
Transmit Register (continued)	Tristate Buffer	Normal	Enable Polarity	Low/high (low default)
			LVTTTL	Output Drive
		Slew Rate		Low/high (high default)
		Enable Polarity		Low/high (low default)
		Pull-Up/-Down		None (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
			Enable Polarity	Low/high (low default)
			Pull-Up/-Down	None (default)
		PCI/PCI-X	Enable Polarity	Low/high (low default)
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
			Enable Polarity	Low/high (low default)
		HSTL	Class	I / II (I default)
			Enable Polarity	Low/high (low default)
		SSTL2/SSTL3	Class	I / II (I default)
			Enable Polarity	Low/high (low default)
		Bidirectional Buffer	Normal	Enable Polarity
	LVTTTL			Output Drive
			Slew Rate	Low/high (high default)
			Enable Polarity	Low/high (low default)
			Pull-Up/-Down	None (default)
	LVCMOS		Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Enable Polarity	Low/high (low default)
			Pull-Up	None (default)
	PCI/PCI-X		None	
			Enable Polarity	Low/high (low default)
	GTL/GTL+		Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
			Enable Polarity	Low/high (low default)
	HSTL		Class	I / II (I default)
			Enable Polarity	Low/high (low default)
	SSTL2/SSTL3	Class	I / II (I default)	
Enable Polarity		Low/high (low default)		

Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.

General Flash Programming Information

Programming Basics

When choosing a programming solution, there are a number of options available. This section provides a brief overview of those options. The next sections provide more detail on those options as they apply to Microsemi FPGAs.

Reprogrammable or One-Time-Programmable (OTP)

Depending on the technology chosen, devices may be reprogrammable or one-time-programmable. As the name implies, a reprogrammable device can be programmed many times. Generally, the contents of such a device will be completely overwritten when it is reprogrammed. All Microsemi flash devices are reprogrammable.

An OTP device is programmable one time only. Once programmed, no more changes can be made to the contents. Microsemi flash devices provide the option of disabling the reprogrammability for security purposes. This combines the convenience of reprogrammability during design verification with the security of an OTP technology for highly sensitive designs.

Device Programmer or In-System Programming

There are two fundamental ways to program an FPGA: using a device programmer or, if the technology permits, using in-system programming. A device programmer is a piece of equipment in a lab or on the production floor that is used for programming FPGA devices. The devices are placed into a socket mounted in a programming adapter module, and the appropriate electrical interface is applied. The programmed device can then be placed on the board. A typical programmer, used during development, programs a single device at a time and is referred to as a single-site engineering programmer.

With ISP, the device is already mounted onto the system printed circuit board when programming occurs. Typically, ISP programming is performed via a JTAG interface on the FPGA. The JTAG pins can be controlled either by an on-board resource, such as a microprocessor, or by an off-board programmer through a header connection. Once mounted, it can be programmed repeatedly and erased. If the application requires it, the system can be designed to reprogram itself using a microprocessor, without the use of any external programmer.

If multiple devices need to be programmed with the same program, various multi-site programming hardware is available in order to program many devices in parallel. Microsemi In House Programming is also available for this purpose.

Programming Features for Microsemi Devices

Flash Devices

The flash devices supplied by Microsemi are reprogrammable by either a generic device programmer or ISP. Microsemi supports ISP using JTAG, which is supported by the FlashPro4 and FlashPro3, FlashPro Lite, Silicon Sculptor 3, and Silicon Sculptor II programmers.

Levels of ISP support vary depending on the device chosen:

- All SmartFusion, Fusion, IGLOO, and ProASIC3 devices support ISP.
- IGLOO, IGLOOe, IGLOO nano V5, and IGLOO PLUS devices can be programmed in-system when the device is using a 1.5 V supply voltage to the FPGA core.
- IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only) or 1.5 V. IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

11 – Security in Low Power Flash Devices

Security in Programmable Logic

The need for security on FPGA programmable logic devices (PLDs) has never been greater than today. If the contents of the FPGA can be read by an external source, the intellectual property (IP) of the system is vulnerable to unauthorized copying. Fusion, IGLOO, and ProASIC3 devices contain state-of-the-art circuitry to make the flash-based devices secure during and after programming. Low power flash devices have a built-in 128-bit Advanced Encryption Standard (AES) decryption core (except for 30 k gate devices and smaller). The decryption core facilitates secure in-system programming (ISP) of the FPGA core array fabric, the FlashROM, and the Flash Memory Blocks (FBs) in Fusion devices. The FlashROM, Flash Blocks, and FPGA core fabric can be programmed independently of each other, allowing the FlashROM or Flash Blocks to be updated without the need for change to the FPGA core fabric.

Microsemi has incorporated the AES decryption core into the low power flash devices and has also included the Microsemi flash-based lock technology, FlashLock.[®] Together, they provide leading-edge security in a programmable logic device. Configuration data loaded into a device can be decrypted prior to being written to the FPGA core using the AES 128-bit block cipher standard. The AES encryption key is stored in on-chip, nonvolatile flash memory.

This document outlines the security features offered in low power flash devices, some applications and uses, as well as the different software settings for each application.

Figure 11-1 • Overview on Security

Generating Programming Files

Generation of the Programming File in a Trusted Environment— Application 1

As discussed in the "Application 1: Trusted Environment" section on page 243, in a trusted environment, the user can choose to program the device with plaintext bitstream content. It is possible to use plaintext for programming even when the FlashLock Pass Key option has been selected. In this application, it is not necessary to employ AES encryption protection. For AES encryption settings, refer to the next sections.

The generated programming file will include the security setting (if selected) and the plaintext programming file content for the FPGA array, FlashROM, and/or FBs. These options are indicated in Table 11-2 and Table 11-3.

Table 11-2 • IGLOO and ProASIC3 Plaintext Security Options, No AES

Security Protection	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	✓	✓	✓
FlashLock only	✓	✓	✓
AES and FlashLock	–	–	–

Table 11-3 • Fusion Plaintext Security Options

Security Protection	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	✓	✓	✓	✓
FlashLock	✓	✓	✓	✓
AES and FlashLock	–	–	–	–

Note: For all instructions, the programming of Flash Blocks refers to Fusion only.

For this scenario, generate the programming file as follows:

1. Select the **Silicon features to be programmed** (Security Settings, FPGA Array, FlashROM, Flash Memory Blocks), as shown in Figure 11-10 on page 248 and Figure 11-11 on page 248. Click **Next**.

If **Security Settings** is selected (i.e., the FlashLock security Pass Key feature), an additional dialog will be displayed to prompt you to select the security level setting. If no security setting is selected, you will be directed to Step 3.

Table 11-5 • FlashLock Security Options for Fusion

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	–	–	–	–
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

For this scenario, generate the programming file as follows:

1. Select only the **Security settings** option, as indicated in Figure 11-14 and Figure 11-15 on page 252. Click **Next**.

Figure 11-14 • Programming IGLOO and ProASIC3 Security Settings Only

IEEE 1532 (JTAG) Interface

The supported industry-standard IEEE 1532 programming interface builds on the IEEE 1149.1 (JTAG) standard. IEEE 1532 defines the standardized process and methodology for ISP. Both silicon and software issues are addressed in IEEE 1532 to create a simplified ISP environment. Any IEEE 1532 compliant programmer can be used to program low power flash devices. Device serialization is not supported when using the IEEE1532 standard. Refer to the standard for detailed information about IEEE 1532.

Security

Unlike SRAM-based FPGAs that require loading at power-up from an external source such as a microcontroller or boot PROM, Microsemi nonvolatile devices are live at power-up, and there is no bitstream required to load the device when power is applied. The unique flash-based architecture prevents reverse engineering of the programmed code on the device, because the programmed data is stored in nonvolatile memory cells. Each nonvolatile memory cell is made up of small capacitors and any physical deconstruction of the device will disrupt stored electrical charges.

Each low power flash device has a built-in 128-bit Advanced Encryption Standard (AES) decryption core, except for the 30 k gate devices and smaller. Any FPGA core or FlashROM content loaded into the device can optionally be sent as encrypted bitstream and decrypted as it is loaded. This is particularly suitable for applications where device updates must be transmitted over an unsecured network such as the Internet. The embedded AES decryption core can prevent sensitive data from being intercepted (Figure 12-1 on page 265). A single 128-bit AES Key (32 hex characters) is used to encrypt FPGA core programming data and/or FlashROM programming data in the Microsemi tools. The low power flash devices also decrypt with a single 128-bit AES Key. In addition, low power flash devices support a Message Authentication Code (MAC) for authentication of the encrypted bitstream on-chip. This allows the encrypted bitstream to be authenticated and prevents erroneous data from being programmed into the device. The FPGA core, FlashROM, and Flash Memory Blocks (FBs), in Fusion only, can be updated independently using a programming file that is AES-encrypted (cipher text) or uses plain text.

3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.

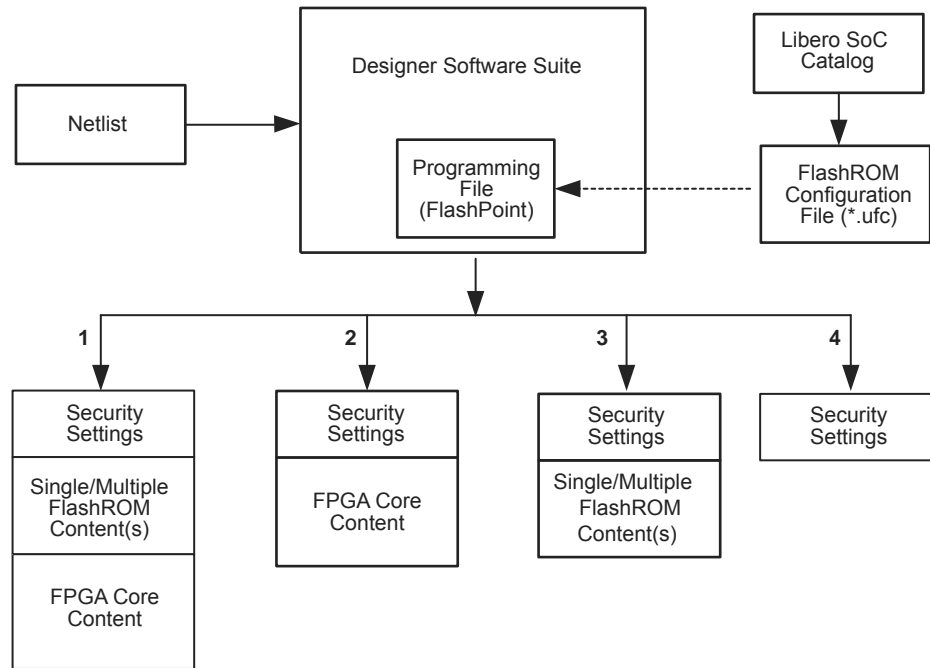


Figure 12-4 • Flexible Programming File Generation for Different Applications

Programming Solution

For device programming, any IEEE 1532-compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock – TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file – STAPL
- Daisy chain – Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming – Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply – The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	This chapter will now be published standalone as an application note in addition to being part of the IGLOO/ProASIC3/Fusion FPGA fabric user's guides (SAR 38769).	N/A
	The "ISP Programming Header Information" section was revised to update the description of FP3-10PIN-ADAPTER-KIT in Table 12-3 • Programming Header Ordering Codes, clarifying that it is the adapter kit used for ProASIC ^{PLUS} based boards, and also for ProASIC3 based boards where a compact programming header is being used (SAR 36779).	269
June 2011	The VPUMP programming mode voltage was corrected in Table 12-2 • Power Supplies. The correct value is 3.15 V to 3.45 V (SAR 30668).	263
	The notes associated with Figure 12-5 • Programming Header (top view) and Figure 12-6 • Board Layout and Programming Header Top View were revised to make clear the fact that IGLOO nano V2 devices can be programmed at 1.2 V (SAR 30787).	269, 271
	Figure 12-6 • Board Layout and Programming Header Top View was revised to include resistors tying TCK and TRST to GND. Microsemi recommends tying off TCK and TRST to GND if JTAG is not used (SAR 22921). RT ProASIC3 was added to the list of device families.	271
	In the "ISP Programming Header Information" section, the kit for adapting ProASIC ^{PLUS} devices was changed from FP3-10PIN-ADAPTER-KIT to FP3-26PIN-ADAPTER-KIT (SAR 20878).	269
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	References to FlashPro4 and FlashPro3X were added to this chapter, giving distinctions between them. References to SmartGen were deleted and replaced with Libero IDE Catalog.	N/A
	The "ISP Architecture" section was revised to indicate that V2 devices can be programmed at 1.2 V VCC with FlashPro4.	261
	SmartFusion was added to Table 12-1 • Flash-Based FPGAs Supporting ISP.	262
	The "Programming Voltage (VPUMP) and VJTAG" section was revised and 1.2 V was added to Table 12-2 • Power Supplies.	263
	The "Nonvolatile Memory (NVM) Programming Voltage" section is new.	263
	Cortex-M3 was added to the "Cortex-M1 and Cortex-M3 Device Security" section.	265
	In the "ISP Programming Header Information" section, the additional header adapter ordering number was changed from FP3-26PIN-ADAPTER to FP3-10PIN-ADAPTER-KIT, which contains 26-pin migration capability.	269
	The description of NC was updated in Figure 12-5 • Programming Header (top view), Table 12-4 • Programming Header Pin Numbers and Description and Figure 12-6 • Board Layout and Programming Header Top View.	269, 270
The "Symptoms of a Signal Integrity Problem" section was revised to add that customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots. "FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems" formerly read, "from 24 MHz down to 1 MHz." "The Scan Chain command expects to see 0x2" was changed to 0x1.	271	

Remote Upgrade via TCP/IP

Transmission Control Protocol (TCP) provides a reliable bitstream transfer service between two endpoints on a network. TCP depends on Internet Protocol (IP) to move packets around the network on its behalf. TCP protects against data loss, data corruption, packet reordering, and data duplication by adding checksums and sequence numbers to transmitted data and, on the receiving side, sending back packets and acknowledging the receipt of data.

The system containing the low power flash device can be assigned an IP address when deployed in the field. When the device requires an update (core or FlashROM), the programming instructions along with the new programming data (AES-encrypted cipher text) can be sent over the Internet to the target system via the TCP/IP protocol. Once the MCU receives the instruction and data, it can proceed with the FPGA update. Low power flash devices support Message Authentication Code (MAC), which can be used to validate data for the target device. More details are given in the "Message Authentication Code (MAC) Validation/Authentication" section.

Hardware Requirement

To facilitate the programming of the low power flash families, the system must have a microprocessor (with access to the device JTAG pins) to process the programming algorithm, memory to store the programming algorithm, programming data, and the necessary programming voltage. Refer to the relevant datasheet for programming voltages.

Security

Encrypted Programming

As an additional security measure, the devices are equipped with AES decryption. AES works in two steps. The first step is to program a key into the devices in a secure or trusted programming center (such as Microsemi SoC Products Group In-House Programming (IHP) center). The second step is to encrypt any programming files with the same encryption key. The encrypted programming file will only work with the devices that have the same key. The AES used in the low power flash families is the 128-bit AES decryption engine (Rijndael algorithm).

Message Authentication Code (MAC) Validation/Authentication

As part of the AES decryption flow, the devices are equipped with a MAC validation/authentication system. MAC is an authentication tag, also called a checksum, derived by applying an on-chip authentication scheme to a STAPL file as it is loaded into the FPGA. MACs are computed and verified with the same key so they can only be verified by the intended recipient. When the MCU system receives the AES-encrypted programming data (cipher text), it can validate the data by loading it into the FPGA and performing a MAC verification prior to loading the data, via a second programming pass, into the FPGA core cells. This prevents erroneous or corrupt data from getting into the FPGA.

Low power flash devices with AES and MAC are superior to devices with only DES or 3DES encryption. Because the MAC verifies the correctness of the data, the FPGA is protected from erroneous loading of invalid programming data that could damage a device (Figure 14-5 on page 289).

The AES with MAC enables field updates over public networks without fear of having the design stolen. An encrypted programming file can only work on devices with the correct key, rendering any stolen files

15 – Boundary Scan in Low Power Flash Devices

Boundary Scan

Low power flash devices are compatible with IEEE Standard 1149.1, which defines a hardware architecture and the set of mechanisms for boundary scan testing. JTAG operations are used during boundary scan testing.

The basic boundary scan logic circuit is composed of the TAP controller, test data registers, and instruction register (Figure 15-2 on page 294).

Low power flash devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register with four fields (LSB, ID number, part number, and version). The boundary scan register observes and controls the state of each I/O pin. Each I/O cell has three boundary scan register cells, each with serial-in, serial-out, parallel-in, and parallel-out pins.

TAP Controller State Machine

The TAP controller is a 4-bit state machine (16 states) that operates as shown in Figure 15-1.

The 1s and 0s represent the values that must be present on TMS at a rising edge of TCK for the given state transition to occur. IR and DR indicate that the instruction register or the data register is operating in that state.

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain HIGH for five TCK cycles. The TRST pin can also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.

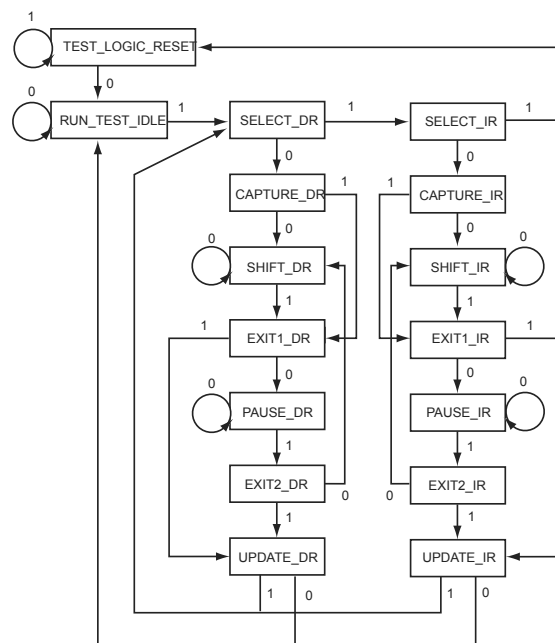


Figure 15-1 • TAP Controller State Machine

Flash Devices Support Power-Up Behavior

The flash FPGAs listed in Table 17-1 support power-up behavior and the functions described in this document.

Table 17-1 • Flash-Based FPGAs

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.